

R-C Thermal Model Parameters

DESCRIPTION

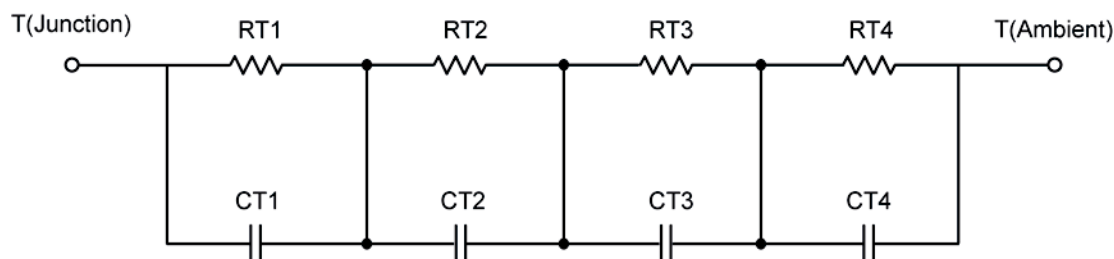
The parametric values in the R-C thermal model have been derived using curve-fitting techniques. These techniques are described in "[A Simple Method of Generating Thermal Models for a Power MOSFET](#)"[1]. When implemented in P-Spice, these values have matching characteristic curves to the Single Pulse Transient Thermal Impedance curves for the MOSFET.

R-C values for the electrical circuit in the Foster/Tank and Cauer/Filter configurations are included.

Note:

For a detailed explanation of implementing these values in P-SPICE, refer to [Application Note AN609 Thermal Simulations Of Power MOSFETs on P-SPICE Platform](#).

R-C THERMAL MODEL FOR TANK CONFIGURATION



R-C VALUES FOR TANK CONFIGURATION			
Thermal Resistance (°C/W)			
Junction to	Ambient	Case	Foot
RT1	214.2990	N/A	79.6144
RT2	24.5623	N/A	15.9707
RT3	98.8378	N/A	116.5748
RT4	90.8922	N/A	124.3247
Thermal Capacitance (Joules/°C)			
Junction to	Ambient	Case	Foot
CT1	5.4751 m	N/A	853.1305 u
CT2	230.4432 u	N/A	121.8111 u
CT3	547.9173 m	N/A	10.5289 m
CT4	1.1544 m	N/A	3.6906 m

This document is intended as a SPICE modeling guideline and does not constitute a commercial product data sheet. Designers should refer to the appropriate data sheet of the same number for guaranteed specification limits.

R-C THERMAL MODEL FOR FILTER CONFIGURATION**R-C VALUES FOR FILTER CONFIGURATION**

Thermal Resistance ($^{\circ}\text{C}/\text{W}$)			
Junction to	Ambient	Case	Foot
RF1	33.8048	N/A	21.3981
RF2	107.4276	N/A	135.9713
RF3	190.3794	N/A	84.0886
RF4	96.8608	N/A	95.2982
Thermal Capacitance (Joules/ $^{\circ}\text{C}$)			
Junction to	Ambient	Case	Foot
CF1	185.7535 u	N/A	95.6622 u
CF2	704.7275 u	N/A	596.9559 u
CF3	4.5727 m	N/A	2.8977 m
CF4	506.5133 m	N/A	3.9614 m

Note: NA indicates not applicable

Reference:

[1] "A Simple Method of Generating Thermal Models for a Power MOSFET" by Wharton McDaniel and Kandarp Pandya. IEEE / SEMITHERM 2002

